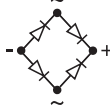
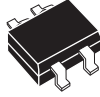




### CBRHDSH2-100

**SURFACE MOUNT SILICON  
HIGH DENSITY  
2.0 AMP DUAL IN LINE  
SCHOTTKY BRIDGE RECTIFIER**

# HD BRIDGE



**HD DIP CASE**

\* Device is **Halogen Free** by design

# Central<sup>TM</sup> Semiconductor Corp.

### DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH2-100 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.

### MARKING CODE: CSH10

### FEATURES:

- Low Leakage Current (700nA TYP @  $V_{RRM}$ )
- High 2.0A Current Rating
- Low  $V_F$  Schottky Diodes (840mV MAX @  $I_F=2.0A$ )

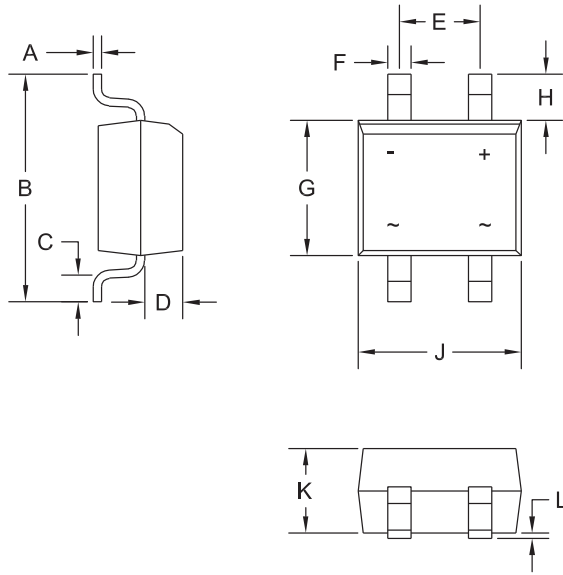
### MAXIMUM RATINGS: ( $T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	V
DC Blocking Voltage	$V_R$	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current, $T_A=75^\circ\text{C}$	$I_O$	2.0	A
Peak Forward Surge Current (8.3ms)	$I_{FSM}$	50	A
Operating Junction Temperature Range	$T_J$	-50 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-50 to +150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS PER DIODE: ( $T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
$I_R$	$V_R=100V$	0.70	4.0	$\mu\text{A}$
$V_F$	$I_F=500\text{mA}$	610		mV
$V_F$	$I_F=1.0A$	700		mV
$V_F$	$I_F=2.0A$	770	840	mV
$C_J$	$V_R=4.0V, f=1.0\text{MHz}$		250	pF

HD DIP CASE - MECHANICAL OUTLINE



R2

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

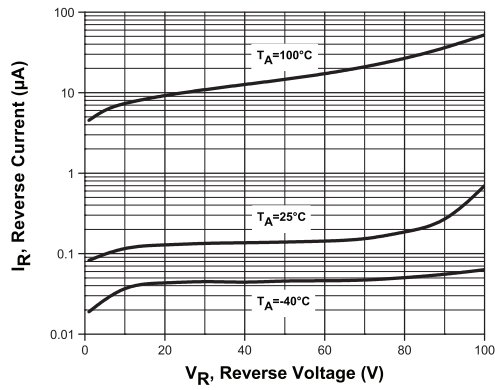
HD DIP (REV: R2)

MARKING CODE: CSH10

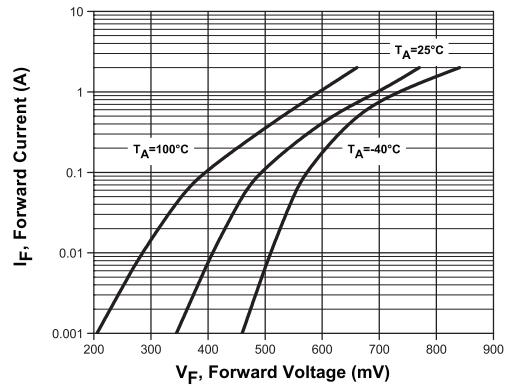
R2 (8-October 2009)

**TYPICAL ELECTRICAL CHARACTERISTICS**

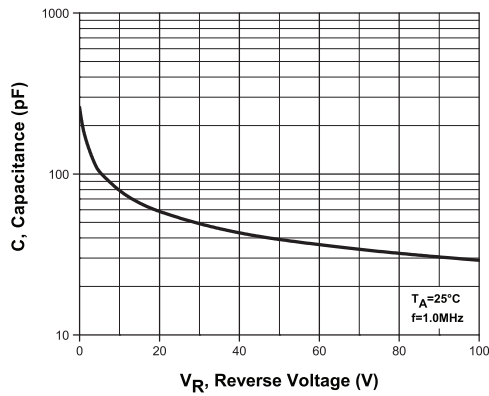
**Typical Per Diode Leakage Current**



**Typical Per Diode Forward Voltage**



**Typical Per Diode Capacitance**



**Per Diode Current Derating**

